# SKiiP 12NAB066V1



3-phase bridge rectifier + brake chopper + 3-phase bridge inverter SKIIP 12NAB066V1

#### Features

Trench IGBTs

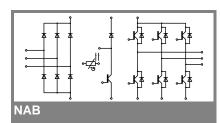
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised file no. E63532

#### **Typical Applications\***

- Inverter up to 5 kVA
- Typical motor power 2,2 kW

#### Remarks

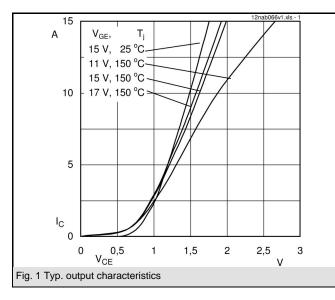
- Case temperature limited to T<sub>C</sub>= 125°C max.
- Product reliability results are valid for T<sub>i</sub>=150°C
- SC data:  $t_p \le 6 \ \mu s; V_{GE} \le 15 \ V; T_j$ = 150°C;  $V_{CC}$  = 360 V
- V<sub>CEsat</sub>, V<sub>F</sub> = chip level values

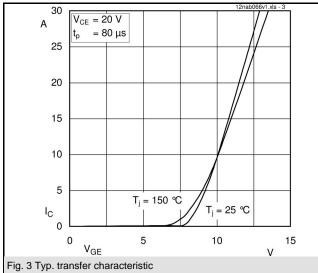


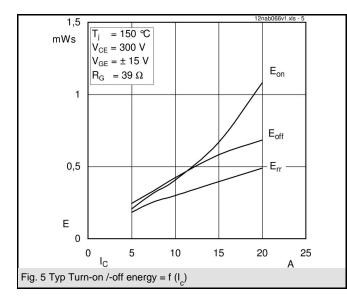
Absolute Maximum Ratings T <sub>S</sub> = 25°C, unless otherwise specif							
Symbol	Conditions	Values	Units				
IGBT - Inverter, Chopper							
V <sub>CES</sub>		600	V				
I <sub>C</sub>	T <sub>s</sub> = 25 (70) °C, T <sub>j</sub> = 150 °C	19 (14)	Α				
I <sub>C</sub>	T <sub>s</sub> = 25 (70) °C, T <sub>j</sub> = 175 °C	20 (16)	Α				
I <sub>CRM</sub>	t <sub>p</sub> = 1 ms	20	Α				
V <sub>GES</sub>		± 20	V				
Diode - Inverter, Chopper							
I <sub>F</sub>	$T_s = 25 (70) \degree C, T_i = 150 \degree C$	20 (15)	Α				
I <sub>F</sub>	T <sub>s</sub> = 25 (70) °C, T <sub>j</sub> = 175 °C	20 (18)	А				
I <sub>FRM</sub>	t <sub>p</sub> = 1 ms	20	А				
Diode - Rectifier							
V <sub>RRM</sub>		800	V				
I <sub>F</sub>	T <sub>s</sub> = 70 °C	35	Α				
I <sub>FSM</sub>	t <sub>p</sub> = 10 ms, sin 180 °, T <sub>j</sub> = 25 °C	220	А				
i²t	t <sub>p</sub> = 10 ms, sin 180 °, T <sub>j</sub> = 25 °C	240	A²s				
I <sub>tRMS</sub>	per power terminal (20 A / spring)	20	A				
T <sub>i</sub>	IGBT, Diode	-40+175	°C				
T <sub>stg</sub>		-40+125	°C				
V <sub>isol</sub>	AC, 1 min.	2500	V				

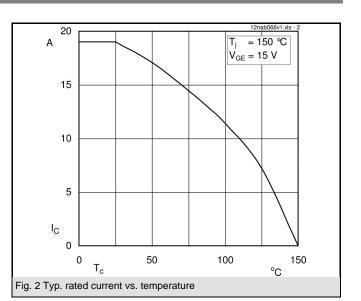
Character	ristics	T <sub>S</sub> = 25°C	$T_S$ = 25°C, unless otherwise specified				
Symbol	Conditions	min.	typ.	max.	Units		
	verter, Chopper						
V <sub>CE(sat)</sub>	I <sub>Cnom</sub> = 10 A, T <sub>j</sub> = 25 (150) °C	1,1	1,45 (1,65)	1,85 (2,05)	V		
V <sub>GE(th)</sub>	$V_{GE} = V_{CE}, I_C = 1 \text{ mA}$		5,8		V		
V <sub>CE(TO)</sub>	T <sub>j</sub> = 25 (150) °C		0,9 (0,7)	1,1 (1)	V		
r <sub>CE</sub>	T <sub>j</sub> = 25 (150) °C		60 (100)	80 (110)	mΩ		
C <sub>ies</sub>	V <sub>CE</sub> = 25 V, V <sub>GE</sub> = 0 V, f = 1 MHz		0,58		nF		
C <sub>oes</sub>	V <sub>CE</sub> = 25 V, V <sub>GE</sub> = 0 V, f = 1 MHz		0,12		nF		
C <sub>res</sub>	V <sub>CE</sub> = 25 V, V <sub>GE</sub> = 0 V, f = 1 MHz		0,04		nF		
R <sub>CC'+EE'</sub>	spring contact-chip T <sub>s</sub> = 25 (150 )°C				mΩ		
R <sub>th(j-s)</sub>	per IGBT		2		K/W		
t <sub>d(on)</sub>	under following conditions		25		ns		
t <sub>r</sub>	V <sub>CC</sub> = 300 V, V <sub>GE</sub> = ±15V		25		ns		
t <sub>d(off)</sub>	I <sub>Cnom</sub> = 10 A, T <sub>j</sub> = 150 °C		190		ns		
t <sub>f</sub>	$R_{Gon} = R_{Goff} = 39 \Omega$		40		ns		
E <sub>on</sub> (E <sub>off</sub> )	inductive load		0,5 (0,3)		mJ		
Diode - In	verter, Chopper						
V <sub>F</sub> = V <sub>EC</sub>	I <sub>F</sub> = 10 A, T <sub>i</sub> = 25 (150) °C		1,3 (1,3)	1,6 (1,6)	V		
V <sub>(TO)</sub>	$T_{i} = 25 (150) ^{\circ}C$		0,9 (0,8)	1 (0,9)	V		
r <sub>T</sub>	T <sub>j</sub> = 25 (150) °C		40 (50)	60 (70)	mΩ		
R <sub>th(j-s)</sub>	per diode		2,5		K/W		
I <sub>RRM</sub>	under following conditions		15,8		Α		
Q <sub>rr</sub>	I <sub>Fnom</sub> = 10 A, V <sub>R</sub> = 300 V		1,5		μC		
E <sub>rr</sub>	V <sub>GE</sub> = 0 V, T <sub>i</sub> = 150°C		0,5		mJ		
	di <sub>F</sub> /dt = 810 Å/µs						
Diode -Re	ectifier						
V <sub>F</sub>	I <sub>Fnom</sub> = 15 A, T <sub>j</sub> = 25 °C		1,1		V		
V <sub>(TO)</sub>	$T_{i} = 150 \ ^{\circ}C$		0,8		V		
r <sub>T</sub>	T <sub>i</sub> = 150 °C		20		mΩ		
R <sub>th(j-s)</sub>	per diode		1,5		K/W		
	ure Sensor	l			I		
R <sub>ts</sub>	3 %, T <sub>r</sub> = 25 (100) °C		1000(1670)		Ω		
Mechanic	· ·	L.					
w		1	35		g		
Ms	Mounting torque	2		2,5	Nm		

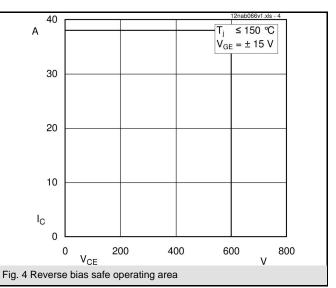
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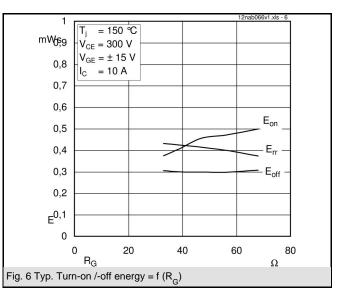




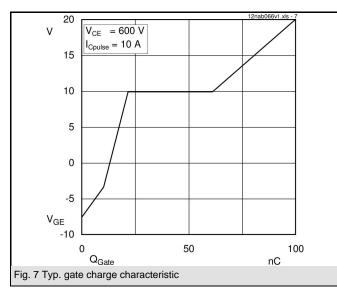


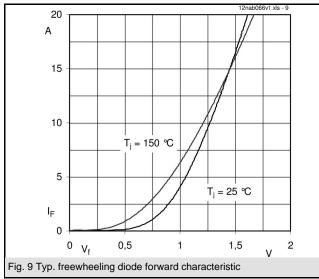


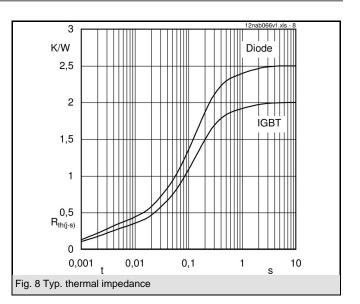


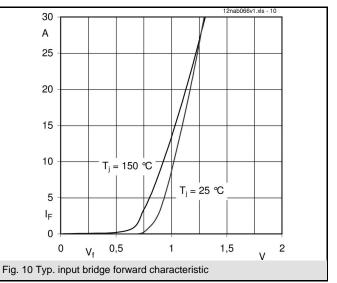


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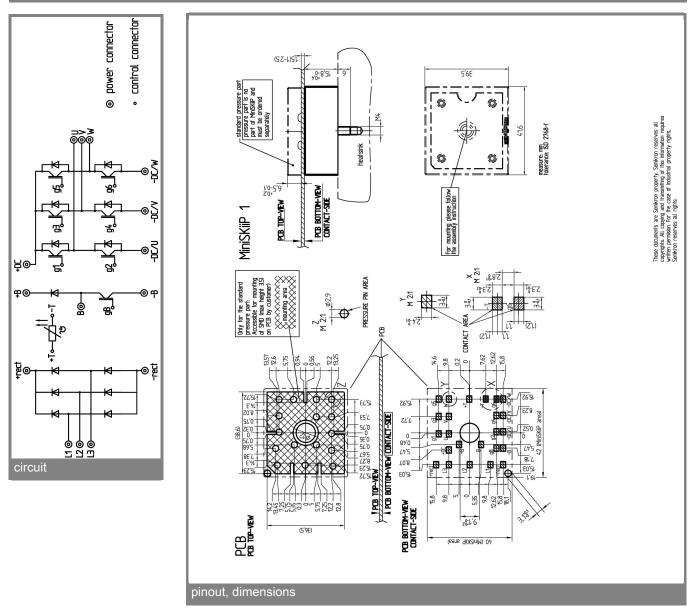








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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

\* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.